Central
Semiconductor Corp.
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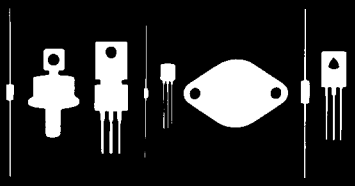
145 Adams Avenue
Hauppauge, New York 11788



2N3819

N-CHANNEL SILICON JUNCTION FET

JEDEC TO-92 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N3819 type is a Silicon N-Channel Junction Field Effect Transistor designed for RF Amplifier and mixer applications.

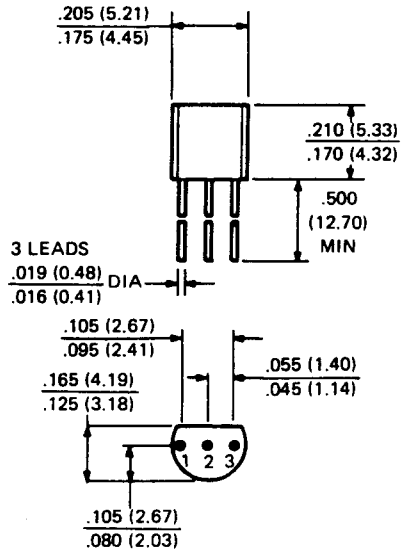
MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNIT
Drain-Gate Voltage	V_{GD}	25	V
Drain-Source Voltage	V_{DS}	25	V
Gate-Source Voltage(Reverse)	V_{GS}	25	V
Gate Current	I_G	10	mA
Power Dissipation	P_D	360	mW
Operating and Storage Junction Temperature	T_J,T_{STG}	-65 TO +150	°C

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_{DSS}	V_{DS}=15V	2	20	mA
I_{GSS}	V_{GS}=15V		2.0	nA
I_{GSS}	V_{GS}=15V, T_A=100°C		2.0	µA
BV_{GSS}	I_G=1.0µA	25		V
V_{GS}	V_{DS}=15V, I_D=200µA	0.5	7.5	V
$V_{GS(OFF)}$	V_{DS}=15V, I_D=2.0nA		8.0	V
C_{iss}	V_{DS}=15V, V_{GS}=0, f=1.0MHz		8.0	pF
C_{rss}	V_{DS}=15V, V_{GS}=0, f=1.0MHz		4.0	pF
|yfs|	V_{DS}=15V, V_{GS}=0, f=1.0MHz	2000	6500	µmho
|yfs|	V_{DS}=15V, V_{GS}=0, f=100MHz	1600		µmho
|yos|	V_{DS}=15V, V_{GS}=0, f=1.0kHz		50	µmho

OUTLINE DRAWING:



LEAD CODE:

1. DRAIN
2. GATE
3. SOURCE

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